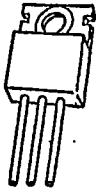


Reference SA01TY23



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# DIGITRON

## SCR

092386  
TY-03

C122

8 A RMS Up to 600 Volts

## MAXIMUM ALLOWABLE RATINGS

Type	Repetitive Peak Off-State Voltage, $V_{DRM}(3)$ $T_C = -40^\circ C$ to $+100^\circ C$	Repetitive Peak Reverse Voltage, $V_{RRM}(1)(3)$ $T_C = -40^\circ C$ to $+100^\circ C$	Non-Repetitive Peak Reverse Voltage, $V_{RSM}(1)(2)$ $T_C = -40^\circ C$ to $+100^\circ C$
C122F	50 Volts	50 Volts	75 Volts
C122A	100 Volts	100 Volts	200 Volts
C122B	200 Volts	200 Volts	300 Volts
C122C	300 Volts	300 Volts	400 Volts
C122D	400 Volts	400 Volts	500 Volts
C122E	500 Volts	500 Volts	600 Volts
C122M	600 Volts	600 Volts	700 Volts

Test	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Peak Off-state or Reverse Current (1)	$I_{DRM}$ or $I_{RRM}$				mA	$V_{DRM} = V_{RRM} = \text{Max. allowable volts peak}$
		—	—	0.1		$T_C = +25^\circ C$
		—	—	0.5		$T_C = +100^\circ C$
Peak-On-State Voltage	$V_{TM}$	—	—	1.83	Volts	$T_C = +25^\circ C$ , $I_{TM} = 16A$ peak, 1 Millisecond wide pulse, Duty cycle $\leq 2\%$
Critical Rate of Rise of Off-State Voltage (Higher values may cause device switching)	$dv/dt$	10	50	—	Volts/ $\mu$ sec	$T_C = +100^\circ C$ , Rated $V_{DRM}$ Gate Open Circuited, Linear Waveform
Circuit Commutated Turn-Off Time	$t_q$	—	50	—	$\mu$ sec	$T_C = +100^\circ C$ , $I_{TM} = 10 A$ peak, Rectangular current pulse, 40 $\mu$ sec duration, Commutation rate = $-5 A/\mu$ sec, Peak reverse voltage = Rated volts max. Reverse voltage at end of turn-off time interval 12 volts min. Repetition rate = 60 pps. Rate of rise of re-applied off-stage voltage ( $dv/dt$ ) = 10 V/ $\mu$ sec. Off-state voltage = Rated V, Gate bias during turn-off time interval = 0 volts, 100 ohms.
D.C. Gate Trigger Current	$I_{GT}$	—	—	25	mA dc	$T_C = +25^\circ C$ $V_D = 6 Vdc$ $R_L = 91$ ohms
		—	—	40		$T_C = -40^\circ C$ $V_D = 6 Vdc$ $R_L = 45$ Ohms
D.C. Gate Trigger Voltage	$V_{GT}$	—	—	1.5	Vdc	$T_C = +25^\circ C$ $V_D = 6 Vdc$ $R_L = 91$ Ohms
		—	—	2.0		$T_C = -40^\circ C$ $V_D = 6 Vdc$ $R_L = 45$ ohms
		0.2	—	—		$T_C = +100^\circ C$ Rated $V_{DRM}$ $R_L = 1000$ ohms
Holding Current	$I_H$				mA dc	Anode source voltage = 24 Vdc, Peak initiating on-state current = 0.5 A, 0.1 msec to 10 msec wide pulse. Gate trigger source = 7V, 20 ohms
		—	—	30		$T_C = +25^\circ C$
		—	—	60		$T_C = -40^\circ C$
Latching Current	$I_L$				mA dc	Main Terminal Source Voltage = 24 Vdc, Gate trigger source = 15V, 100 ohms, 50 $\mu$ sec rise and fall times max.
		—	—	60		$T_C = +25^\circ C$
		—	—	120		$T_C = -40^\circ C$
Steady-State (2) Thermal Resistance					$^\circ C/Watt$	
	$R_{\theta JC}$	—	—	1.8		Junction to Case
	$R_{\theta JA}$	—	—	75		Junction to Ambient